

Carold A1
a ridge structure made of insulating material formed on an upper surface of the second gate electrode but not on an upper surface of the first gate electrode, said ridge structure extending along side edges of the second gate electrode.

A2
6. (Amended) A semiconductor device according to claim 4, further comprising a metal silicide film covering an upper surface of the first gate electrode of said second field effect transistor excepting the upper surface ~~not~~ formed with said ridge structure.

A3
9. (Amended) A semiconductor device comprising:
a first field effect transistor having a first gate electrode formed on a first section of a semiconductor substrate;
a second field effect transistor having a second gate electrode formed on a second section of said semiconductor substrate;
a first film made of a first material and disposed on the second gate electrode of said second field effect transistor, an outer periphery of said first film being aligned with side edges of the second gate electrode;
a second film disposed on said first film, an outer periphery of said second film positioning inside the outer periphery of said first film, and said second film being made of a second material having an etching resistance different from the first material; and

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A3*
a third film disposed on the first gate electrode of said first field effect transistor, an outer periphery of said third film being aligned with side edges of the first gate electrode, said third film being made of the second material.

Please **ADD** the following new claim:

11. (New) A semiconductor device comprising:

A4
a field effect transistor having a gate electrode formed on a first section of a semiconductor substrate;

a ridge structure made of insulating material formed on an upper surface of the gate electrode, said ridge structure extending along side edges of the gate electrode.
